

Form PTO-1449			U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-532	SERIAL NO. 09/332,271	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT Klaus Peter Schuckhof et al.				
			FILING DATE June 11, 1999		GROUP 2812		
U.S. PATENT DOCUMENTS							
*Examiner Initials		Document Number	Date	Notice	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
RP	AN	Ohnishi, K. et al., Improving Gate Oxide Integrity (GOI) of a $W/W$ individual-poly Si Slack-gate by Using Wet-Hydrogen Oxidation in 0.14- $\mu$ m CMOS devices, IEDM, 1998, pgs. 397-400.					
RP	AO	Kawada, K. et al., Water Vapor Generator By catalytic Reactor, pgs. 10-16.					
RP	AP	Wakabayashi, H. et al., An Ultra-Low Resistance and Thermo Stable W/pn-Poly-Si Gate CMOS Technology using Si/TiN Buffer Layer.					
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RP		Hiura, Y. et al., Integration Technology of Polyimide ( $W/W$ SiN/Poly-Si) Dual Gate CMOS for 1 Gbit DRAMs and Beyond, IEDM, 1998.					
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RP		Lee, B. et al., In-situ Barrier Formation for High Reliable $W$ /barrier/poly-Si Gate Using Denudation of $W$ on Polycrystalline Si, IEDM, 1998 pgs. 385-389.					
Ron Pompey			4-23-04				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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